



Micro Commercial Components



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SI2302

Features

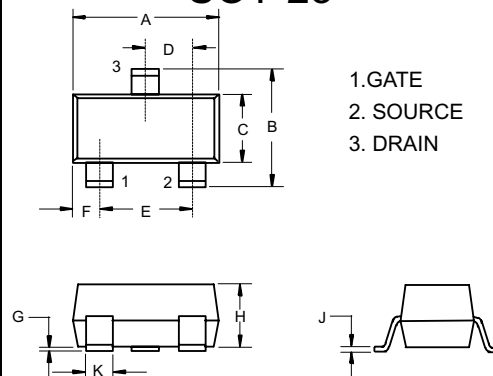
- Halogen free available upon request by adding suffix "-HF"
- 20V,3.0A, $R_{DS(ON)}=55m\Omega$ @ $V_{GS}=4.5V$
 $R_{DS(ON)}=82m\Omega$ @ $V_{GS}=2.5V$
- High dense cell design for extremely low $R_{DS(ON)}$
- Rugged and reliable
- Lead free product is acquired
- SOT-23 Package
- Marking Code: S2
- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level 1

Maximum Ratings @ 25°C Unless Otherwise Specified

Symbol	Parameter	Rating	Unit
V_{DS}	Drain-source Voltage	20	V
I_D	Drain Current-Continuous	3	A
I_{DM}	Drain Current-Pulsed ^a	10	A
V_{GS}	Gate-source Voltage	± 8	V
P_D	Total Power Dissipation	1.25	W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient ^b	100	°C/W
T_J	Operating Junction Temperature	-55 to +150	°C
T_{STG}	Storage Temperature	-55 to +150	°C

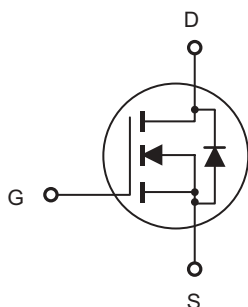
N-Channel Enhancement Mode Field Effect Transistor

SOT-23

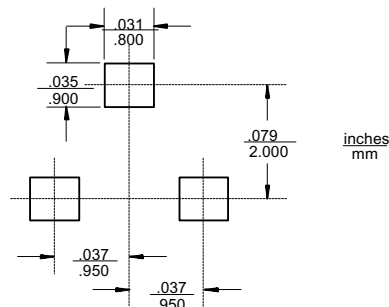


DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.110	.120	2.80	3.04	
B	.083	.104	2.10	2.64	
C	.047	.055	1.20	1.40	
D	.035	.041	.89	1.03	
E	.070	.081	1.78	2.05	
F	.018	.024	.45	.60	
G	.0005	.0039	.013	.100	
H	.035	.044	.89	1.12	
J	.003	.007	.085	.180	
K	.015	.020	.37	.51	

Internal Block Diagram



Suggested Solder Pad Layout





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Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0V, I_D = 10\mu A$	20			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1	μA
Gate Body Leakage Current, Forward	I_{GSSF}	$V_{GS} = 8V, V_{DS} = 0V$			100	nA
Gate Body Leakage Current, Reverse	I_{GSSR}	$V_{GS} = -8V, V_{DS} = 0V$			-100	nA
On Characteristics ^c						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}, I_D = 50\mu A$	0.65		1.2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 3.6A$		55	72	m Ω
On-Resistance		$V_{GS} = 2.5V, I_D = 3.1A$		82	110	m Ω
Forward Transconductance	g_{FS}	$V_{DS} = 5V, I_D = 3.6A$		8.5		S
Dynamic Characteristics ^d						
Input Capacitance	C_{iss}	$V_{DS} = 10V, V_{GS} = 0V, f = 1.0\text{ MHz}$		237		pF
Output Capacitance	C_{oss}			120		pF
Reverse Transfer Capacitance	C_{rss}			45		pF
Switching Characteristics ^d						
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10V, I_D = 3.6A, V_{GS} = 4.5V, R_{GEN} = 6\Omega$		23	45	ns
Turn-On Rise Time	t_r			11	30	ns
Turn-Off Delay Time	$t_{d(off)}$			34	70	ns
Turn-On Fall Time	t_f			36	70	ns
Total Gate Charge	Q_g	$V_{DS} = 10V, I_D = 3.6A, V_{GS} = 4.5V$		6	10	nC
Gate-Source Charge	Q_{gs}			1.4		nC
Gate-Drain Charge	Q_{gd}			1.8		nC
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Current ^b	I_S				0.94	A
Drain-Source Diode Forward Voltage ^c	V_{SD}	$V_{GS} = 0V, I_S = 0.94A$			1.2	V
Notes :						
a.Repetitive Rating : Pulse width limited by maximum junction temperature.						
b.Surface Mounted on FR4 Board, $t \leq 10\text{ sec}$.						
c.Pulse Test : Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.						
d.Guaranteed by design, not subject to production testing.						

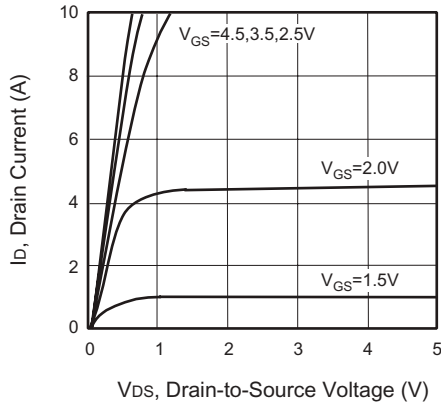


Figure 1. Output Characteristics

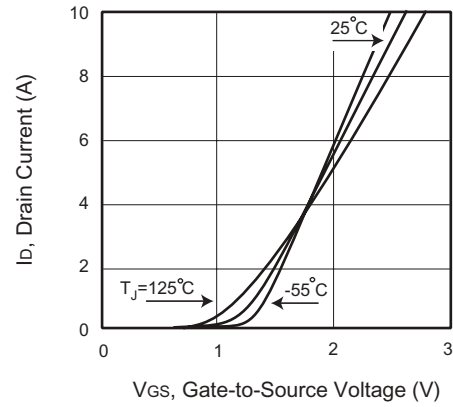


Figure 2. Transfer Characteristics

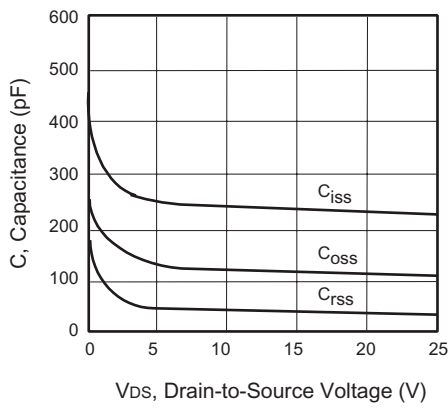


Figure 3. Capacitance

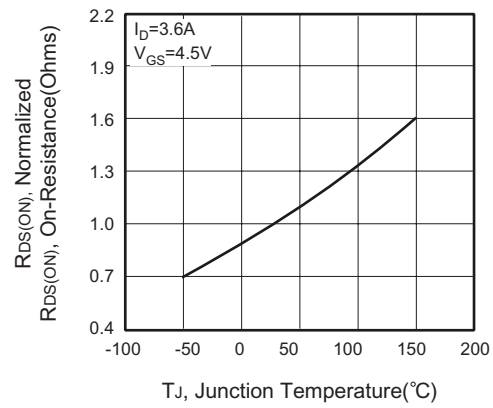


Figure 4. On-Resistance Variation with Temperature

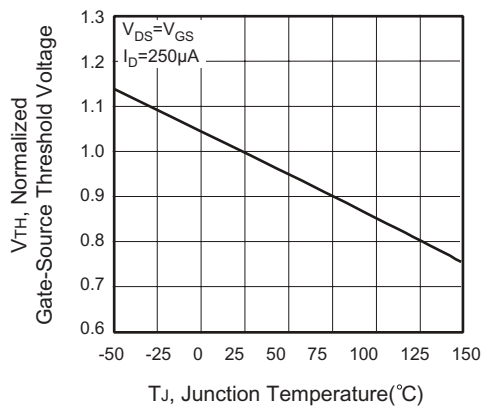


Figure 5. Gate Threshold Variation with Temperature

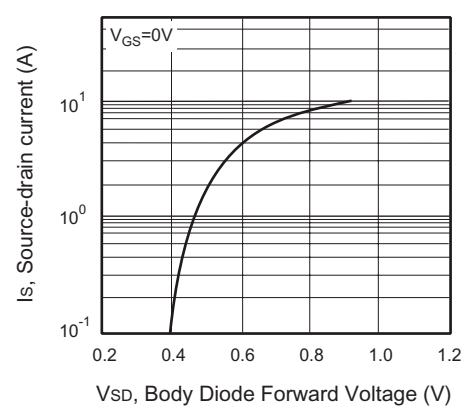


Figure 6. Body Diode Forward Voltage Variation with Source Current